To all our customers

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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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Keep safety first in your circuit designs!

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HSN278WK

Silicon Epitaxial Schottky Barrier Diode

RENESAS

ADE-208-1524 (Z)

Rev.0
May. 2002

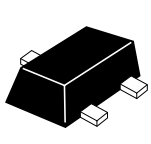
Features

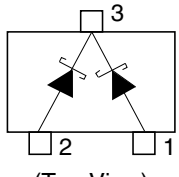
- Low forward voltage, Low capacitance.
- Miniature Flat Lead Package (MFPAK) is suitable for surface mount design.

Ordering Information

Type No.	Laser Mark	Package Code
HSN278WK	SI–	MFPAK

Pin Arrangement





(Top View)

1. Anode
2. Anode
3. Cathode

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Value	Unit
Repetitive peak reverse voltage	V_{RRM}	30	V
Reverse voltage	V_R	30	V
Non-Repetitive peak forward surge current	I_{FSM} *	200	mA
Peak forward current	I_{FM}	150	mA
Average rectified current	I_O	30	mA
Junction temperature	Tj	125	°C
Storage temperature	Tstg	–55 to +125	°C

Note: 10 ms sine wave 1 pulse one device.

Electrical Characteristics

(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	V_{F1}	—	—	0.30	V	I_F = 1 mA
	V_{F2}	—	—	0.95		I_F = 30 mA
Reverse current	I_R	—	—	700	nA	V_R = 10 V
Capacitance	C	—	—	1.50	pF	V_R = 1 V, f = 1 MHz
ESD-Capability *[1]	—	100	—	—	V	C = 200 pF, R_L = 0 Ω, Both forward and reverse each 1 shot.

Notes: 1. Failure criterion ; I_R > 1.4 μA at V_R = 10 V

2. Please do not use the soldering iron due to avoid high stress to the MFPAK package.

Main Characteristics

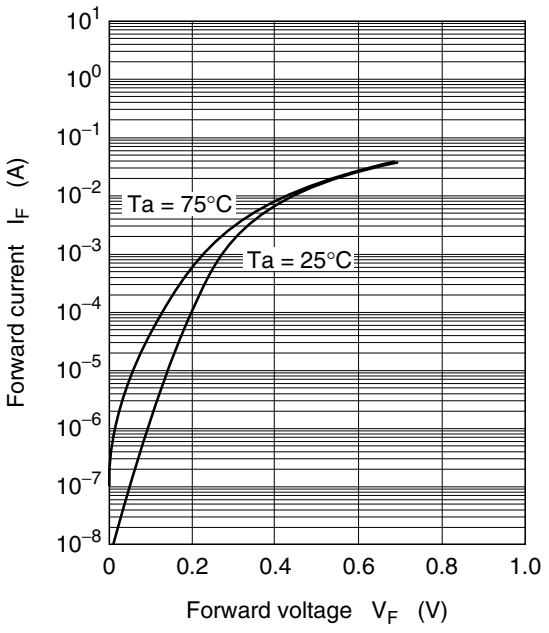


Fig.1 Forward current Vs. Forward voltage

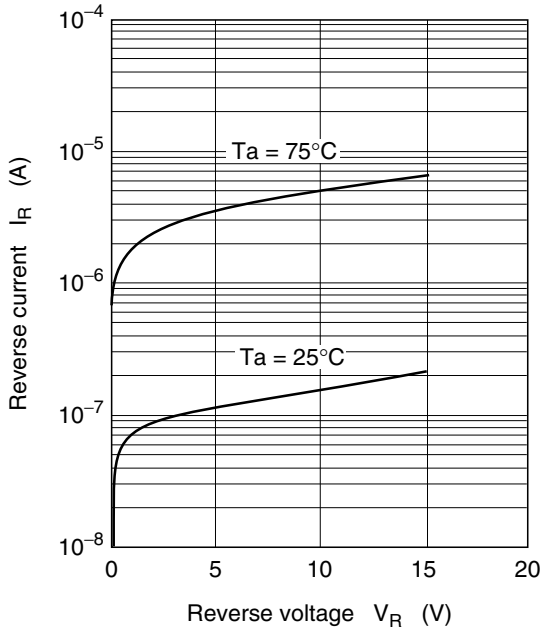


Fig.2 Reverse current Vs. Reverse voltage

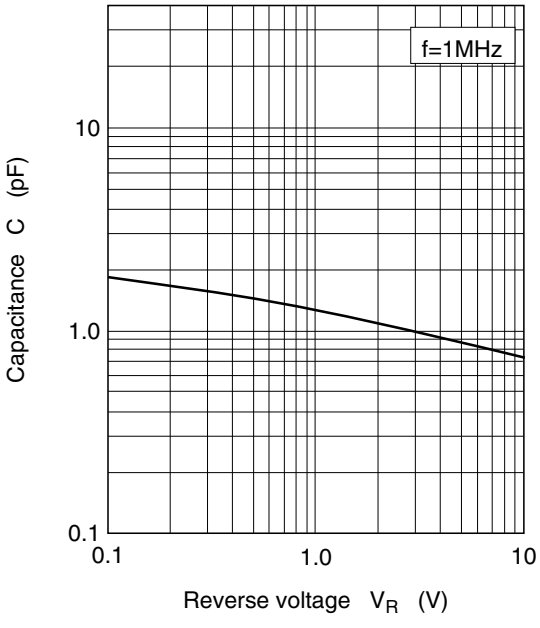
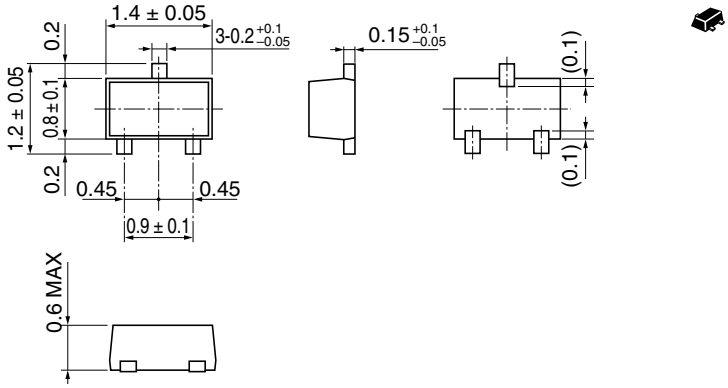


Fig.3 Capacitance Vs. Reverse voltage

Package Dimensions

As of January, 2002

Unit: mm



Hitachi Code	MFPAK
JEDEC	—
JEITA	—
Mass (reference value)	0.0016 g

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